

2SK1838 L, 2SK1838 S

Silicon N Channel MOS FET

Application

High speed power switching

Features

- Low on-resistance
- High speed switching
- Low drive current
- No secondary breakdown
- Suitable for switching regulator, DC-DC converter

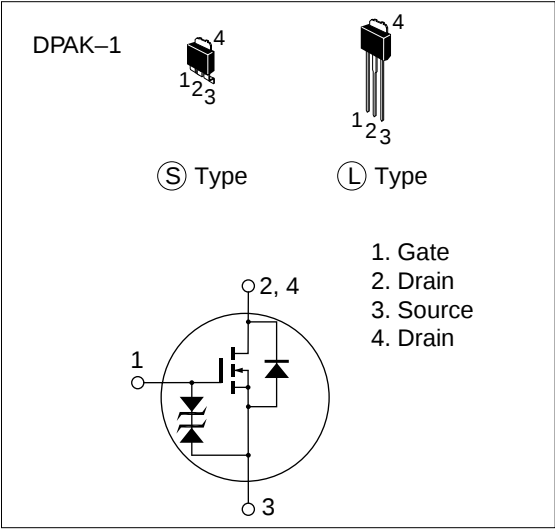


Table 1 Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	250	V
Gate to source voltage	V_{GSS}	± 30	V
Drain current	I_D	1	A
Drain peak current	$I_{D(pulse)}^*$	2	A
Body-drain diode reverse drain current	I_{DR}	1	A
Channel dissipation	P_{ch}^{**}	10	W
Channel temperature	T_{ch}	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

* $PW \leq 10 \mu s$, duty cycle $\leq 1 \%$

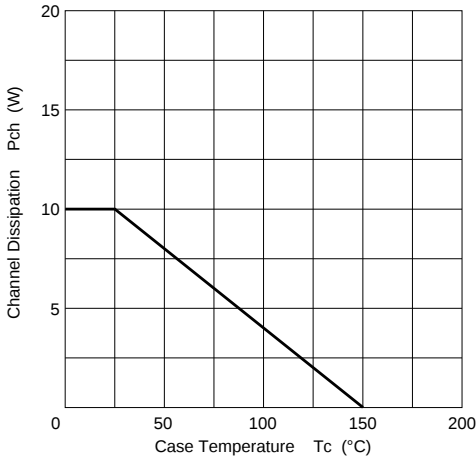
** Value at $T_c = 25 \text{ }^\circ\text{C}$

Table 2 Electrical Characteristics (Ta = 25°C)

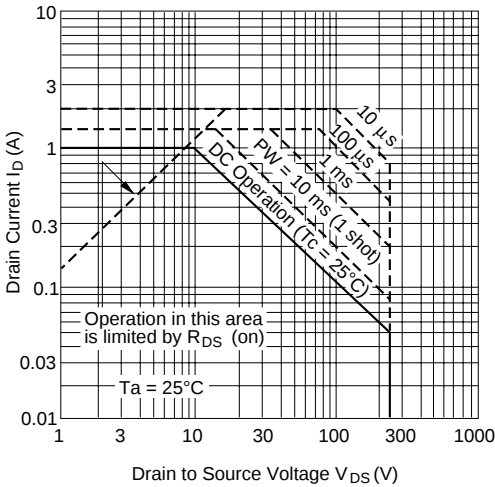
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	250	—	—	V	$I_D = 10 \text{ mA}$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	± 30	—	—	V	$I_G = \pm 100 \text{ }\mu\text{A}$, $V_{DS} = 0$
Gate to source leak current	I_{GSS}	—	—	± 10	μA	$V_{GS} = \pm 25 \text{ V}$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	50	μA	$V_{DS} = 200 \text{ V}$, $V_{GS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	2.0	—	3.0	V	$I_D = 1 \text{ mA}$, $V_{DS} = 10 \text{ V}$
Static drain to source on state resistance	$R_{DS(on)}$	—	5.5	8.0	Ω	$I_D = 0.5 \text{ A}$ $V_{GS} = 10 \text{ V}^*$
Forward transfer admittance	$ y_{fs} $	0.3	0.5	—	S	$I_D = 0.5 \text{ A}$ $V_{DS} = 10 \text{ V}^*$
Input capacitance	C_{iss}	—	60	—	pF	$V_{DS} = 10 \text{ V}$
Output capacitance	C_{oss}	—	30	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	C_{rss}	—	5	—	pF	$f = 1 \text{ MHz}$
Turn-on delay time	$t_{d(on)}$	—	5	—	ns	$I_D = 0.5 \text{ A}$
Rise time	t_r	—	6	—	ns	$V_{GS} = 10 \text{ V}$
Turn-off delay time	$t_{d(off)}$	—	10	—	ns	$R_L = 60 \text{ }\Omega$
Fall time	t_f	—	4.5	—	ns	
Body-drain diode forward voltage	V_{DF}	—	0.96	—	V	$I_F = 1 \text{ A}$, $V_{GS} = 0$
Body-drain diode reverse recovery time	t_{rr}	—	160	—	ns	$I_F = 1 \text{ A}$, $V_{GS} = 0$, $di_F / dt = 100 \text{ A} / \mu\text{s}$

* Pulse Test

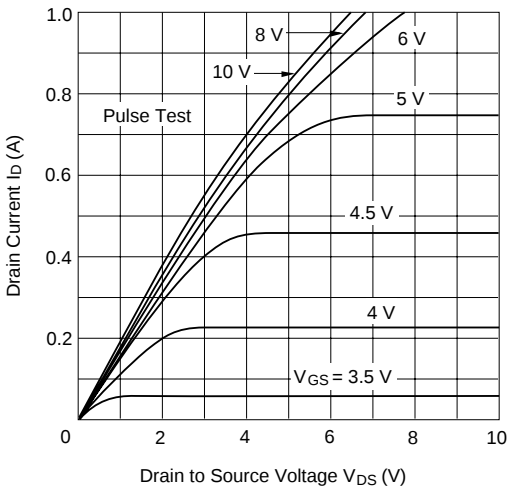
Power vs. Temperature Derating



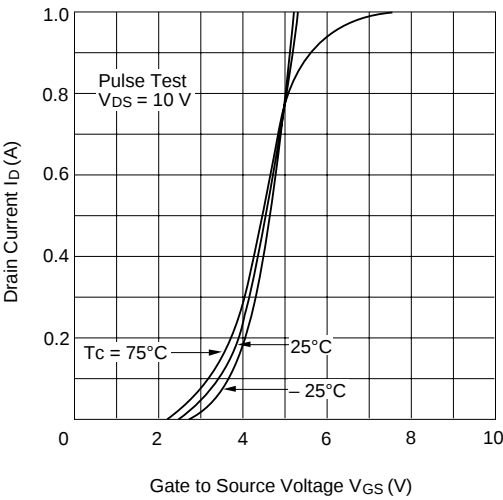
Maximum Safe Operation Area



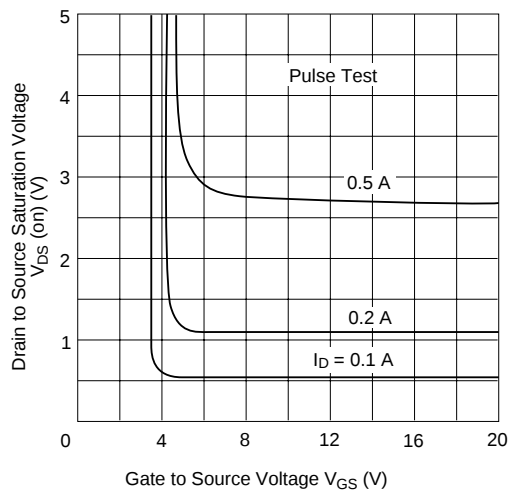
Typical Output Characteristics



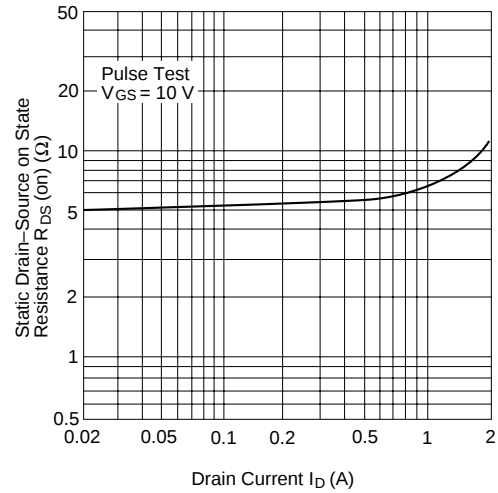
Typical Transfer Characteristics



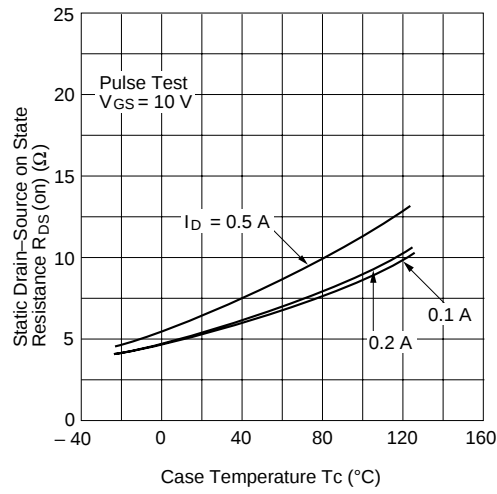
Drain-Source Saturation Voltage vs.
Gate-Source Voltage



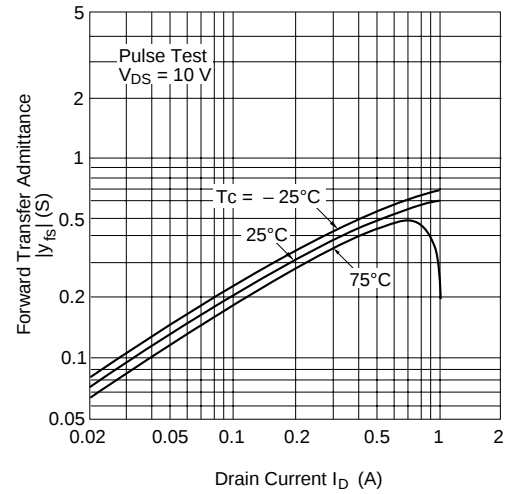
Static Drain-Source on State
Resistance vs. Drain Current



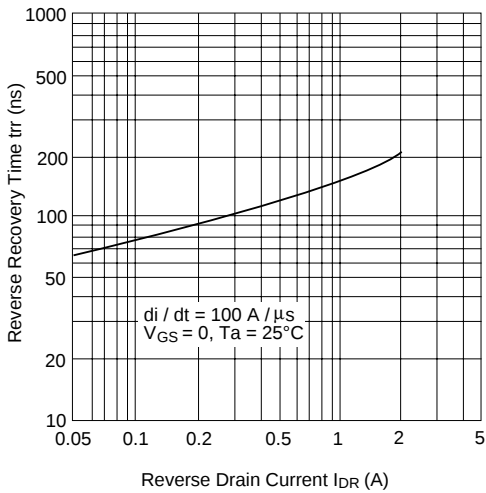
Static Drain-Source on State
Resistance vs. Temperature



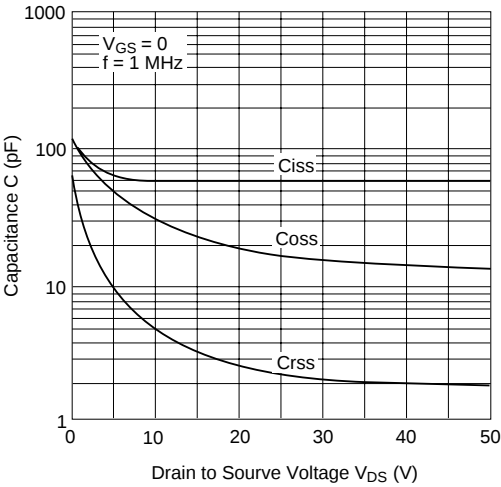
Forward Transfer Admittance vs.
Drain Current



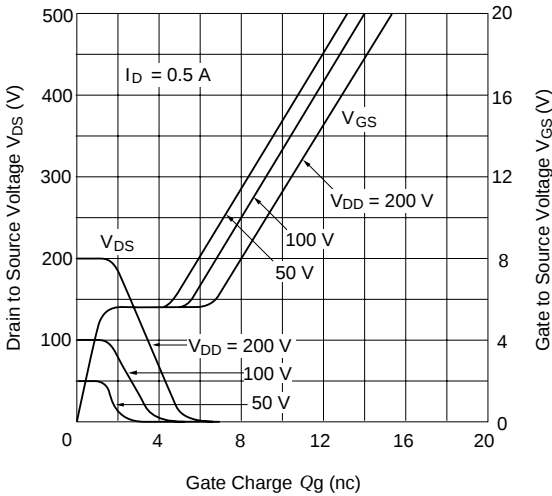
Body-Drain Diode Reverse Recovery Time



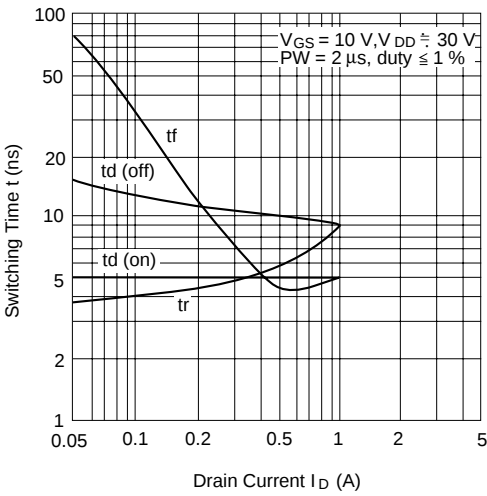
Typical Capacitance vs. Drain-Source Voltage

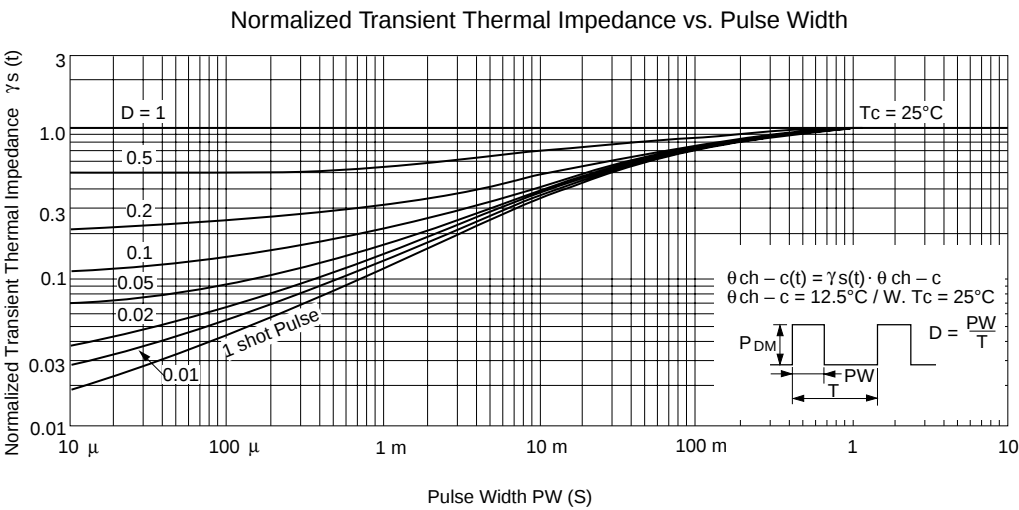
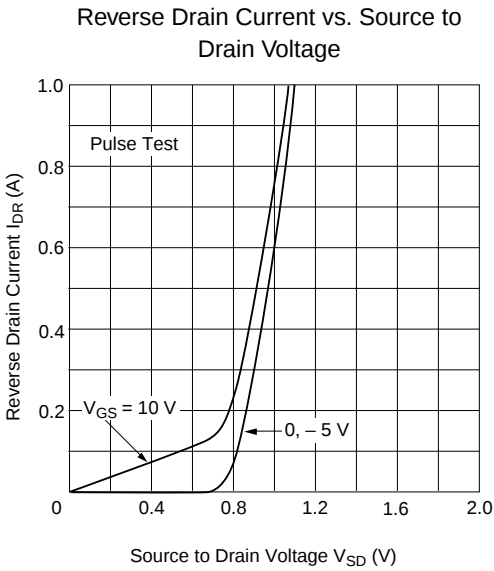


Dynamic Input Characteristics

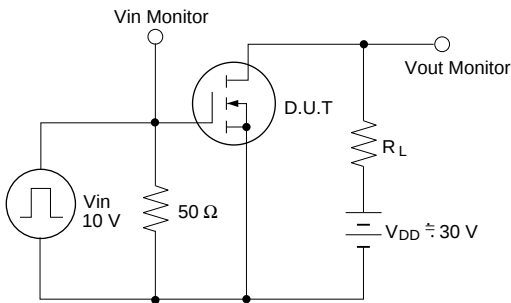


Switching Characteristics





Switching Time Test Circuit



Waveforms

